Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 40 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)} 25 A				
V _{DRM} /V _{RRM}	1200 V			
V _{TM}	1.6 V			
I _{GT}	35 mA			
TJ	-40 °C to 140 °C			
Package	3L TO-220AB			
Circuit configuration	Single SCR			

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 140 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-40TTS12... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 140 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	RAMETER TEST CONDITIONS VALUES						
I _{T(AV)}	Sinusoidal waveform	25	А				
I _{RMS}		40	A				
V _{RRM} /V _{DRM}		1200	V				
I _{TSM}		350	А				
V _T	$T_J = 25 \ ^{\circ}C$	1.6	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		-40 to +140	°C				

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	TJ ℃			
VS-40TTS12-M3	1200	1200	-25 to +140			



FREE

VS-40TTS12-M3



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CON	VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 93 ^{\circ}{\rm C}, 180^{\circ} {\rm conduct}$	tion half sine wave	25		
Maximum RMS on-state current	I _{RMS}			40	А	
Maximum peak, one-cycle	l	10 ms sine pulse, rated V	RRM applied	300	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volt	age reapplied	350		
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V	RRM applied	450	A ² s	
Maximum i-t for fusing	1-1	10 ms sine pulse, no volt	age reapplied	630	A-s	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no volta	6300	A²√s		
Maximum on-state voltage	V _{TM}	80 A, T _J = 25 °C		1.6	V	
Low level value of on-state slope resistance	r _t	T _{.1} = 140 °C		11.4	mΩ	
Low level value of threshold voltage	V _{T(TO)}	1j = 140 C		0.96	V	
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	$V = \text{Reted} V = \Lambda V$	0.5		
current	I _{RRM} /I _{DRM}	T _J = 140 °C	$V_{R} = Rated V_{RRM} / V_{DRM}$	12		
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		100	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C		200		
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max., linear to 80 °C, V _{DRM} = R _g - k = Open		500	V/µs	
Maximum rate of rise of turned-on current	dl/dt			150	A/µs	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	w
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+ I _{GM}		1.5	А
Maximum peak negative gate voltage	- V _{GM}		10	V
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	35	mA
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	1.3	V
Maximum DC gate voltage not to trigger	V _{GD}	$T_{I} = 140 \text{ °C}, V_{DBM} = \text{Rated value}$	0.2	
Maximum DC gate current not to trigger	I _{GD}	$i_{\rm J} = 140$ O, $v_{\rm DRM} = hated value$	1.5	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T _{.1} = 140 °C	4	μs
Typical turn-off time	t _q	1j = 140 C	110	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage T _J , T _{Stg}			-40 to 140	°C		
Maximum thermal resistance, junction to case	stance, R _{thJC} DC operation		0.8			
Maximum thermal resistance, junction to ambient		R _{thJA}		60	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Maunting targue				6 (5)	kgf ⋅ cm	
Mounting torque	maximum			12 (10)	(lbf ⋅ in)	
Marking device Case style 3L TO-220AB 40TTS12		FS12				

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Document Number: 96289

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



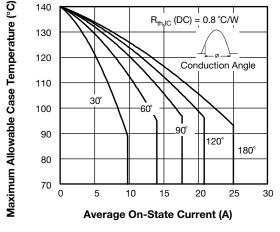


Fig. 1 - Current Rating Characteristics

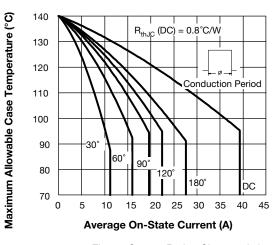


Fig. 2 - Current Rating Characteristics

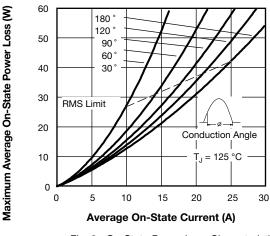


Fig. 3 - On-State Power Loss Characteristics



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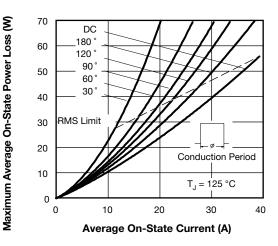


Fig. 4 - On-State Power Loss Characteristics

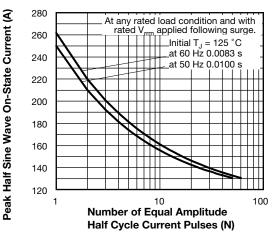


Fig. 5 - Maximum Non-Repetitive Surge Current

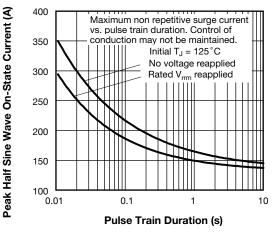


Fig. 6 - Maximum Non-Repetitive Surge Current

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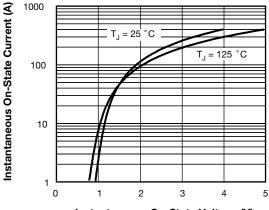
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VS-40TTS12-M3

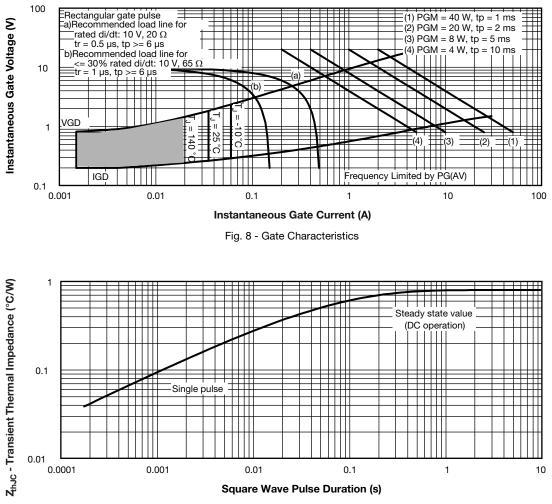






Instantaneous On-State Voltage (V)

Fig. 7 - On-State Voltage Drop Characteristics







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ORDERING INFORMATION TABLE

Device code	VS-	40	т	т	S	12	-M3
Device code	V3-	40			3	12	-1413
		(2)	(3)	(4)	(5)	(6)	(7)
	\bigcirc		\bigcirc	4	\bigcirc	\bigcirc	(\mathbf{r})
	1 ·	- Visł	nay Sem	niconduc	tors pro	duct	
	2 -	- Cur	rent rati	ng, RMS	s value		
	3 -	- Circ	uit confi	iguratior	1:		
		T =	single th	nyristor			
	4 -	- Pac	kage:				
		T =	TO-220				
	5 -	- Тур	e of silio	con:			
	_			d recove	•		
	6 -	- Volt	age rati	ng (12 =	1200 V)	
	7 -	- Envi	ronmen	tal digit:			
		-M3	= halog	en-free,	RoHS-c	ompliar	nt, and t

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TTS12-M3	50	1000	Antistatic plastic tubes			

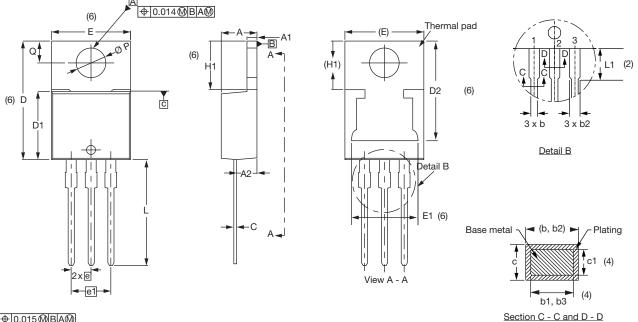
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



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3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INCHES		NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC [®]	outline	TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

- ⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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